

Zhen Zhu

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	A channel-potential-based surface potential model and a turn-on DC channel-potential-based drain current model for fully-depleted poly-Si thin film transistors including tail and deep acceptor-like trap states in bulk. <i>Modern Physics Letters B</i> , 2020, 34, 2050023.	1.9	0
2	SURFACE POTENTIAL DISTRIBUTION MODEL BASED ON ANALYTICAL CHANNEL POTENTIAL APPROXIMATION FOR ULTRA-THIN BODY POLY-SI THIN FILM TRANSISTORS IN LINEAR REGION. <i>Surface Review and Letters</i> , 2017, 24, 1750108.	1.1	1
3	Approximate analytical channel potential model of poly-Si thin film transistors operated in the strong inversion region under the high gate and low drain biases. <i>Journal of Physics: Conference Series</i> , 2015, 574, 012100.	0.4	3
4	Analysis of the current conduction in poly-Si thin film transistors. <i>Semiconductor Science and Technology</i> , 2013, 28, 015017.	2.0	2
5	QUASI TWO-DIMENSIONAL ANALYSIS OF THE SURFACE POTENTIAL FOR POLY-Si THIN FILM TRANSISTORS BASED ON THE CHANNEL POTENTIAL. <i>International Journal of Modern Physics B</i> , 2012, 26, 1250069.	2.0	4
6	Thermally generated leakage current mechanisms of metal-induced laterally crystallized n-type poly-Si TFTs under hot-carrier stress. <i>Solid-State Electronics</i> , 2011, 62, 62-66.	1.4	2
7	Field-enhanced-generated leakage current of metal-induced laterally crystallized hydrogenated n-type poly-Si TFTs under hot-carrier stress. <i>Semiconductor Science and Technology</i> , 2009, 24, 085015.	2.0	2